

VRW056 QSQ Silicon NPN transistor in a SOT-23 Plastic Package.

$k_{IH}/Y_{FHR}/5VD; 45$
High h_{FE} and V_{CEO} , complementary pair with 2SA812.

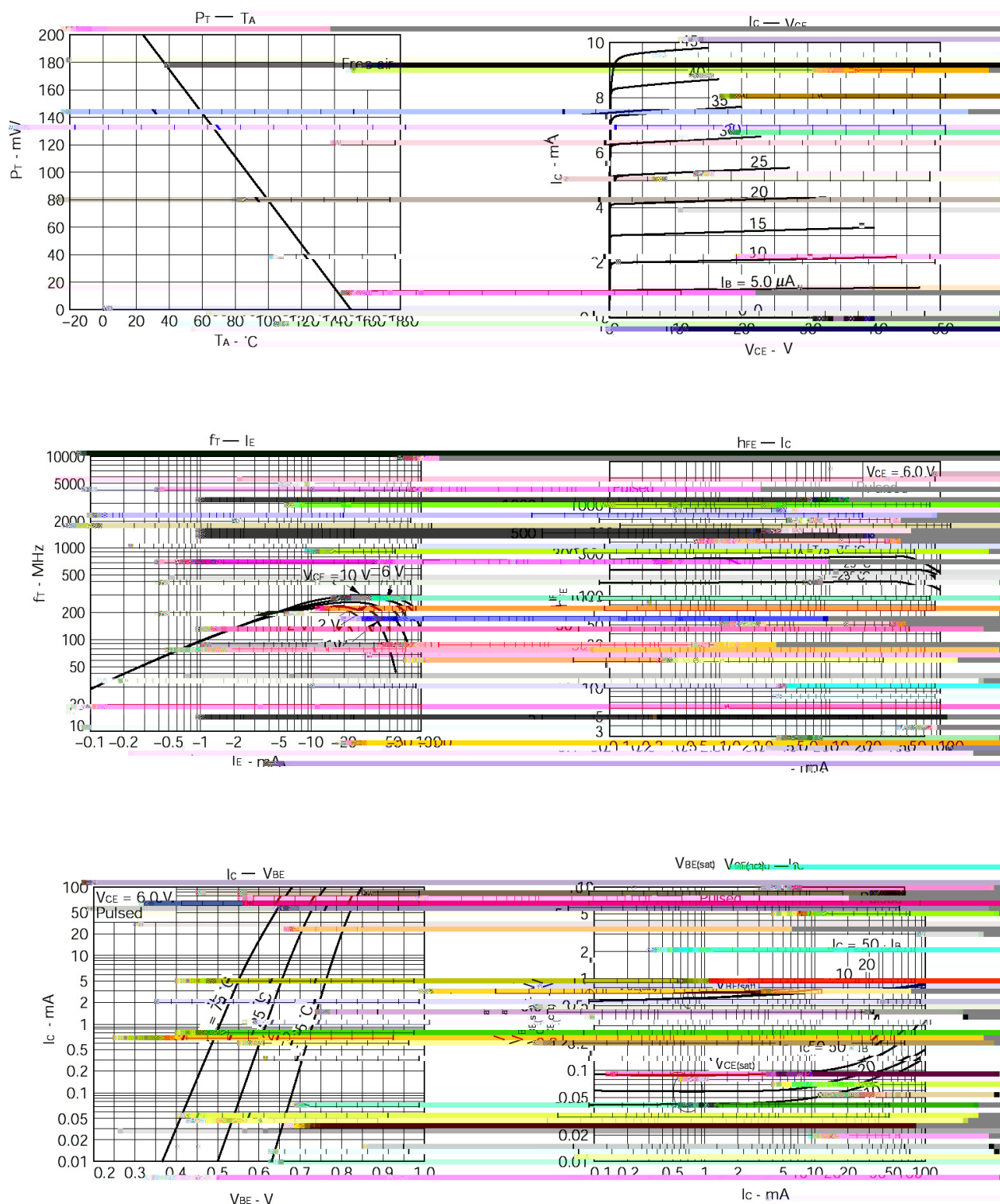
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	A
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	A
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	90	200	600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.15	0.3	V
Base to Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.86	1.0	V
Base Emitter Voltage	V_{BE}	$V_{CE}=6.0V$ $I_C=1.0mA$	0.55	0.62	0.65	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_E=10mA$		250		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $I_E=0$ $f=1.0MHz$		3.0		pF

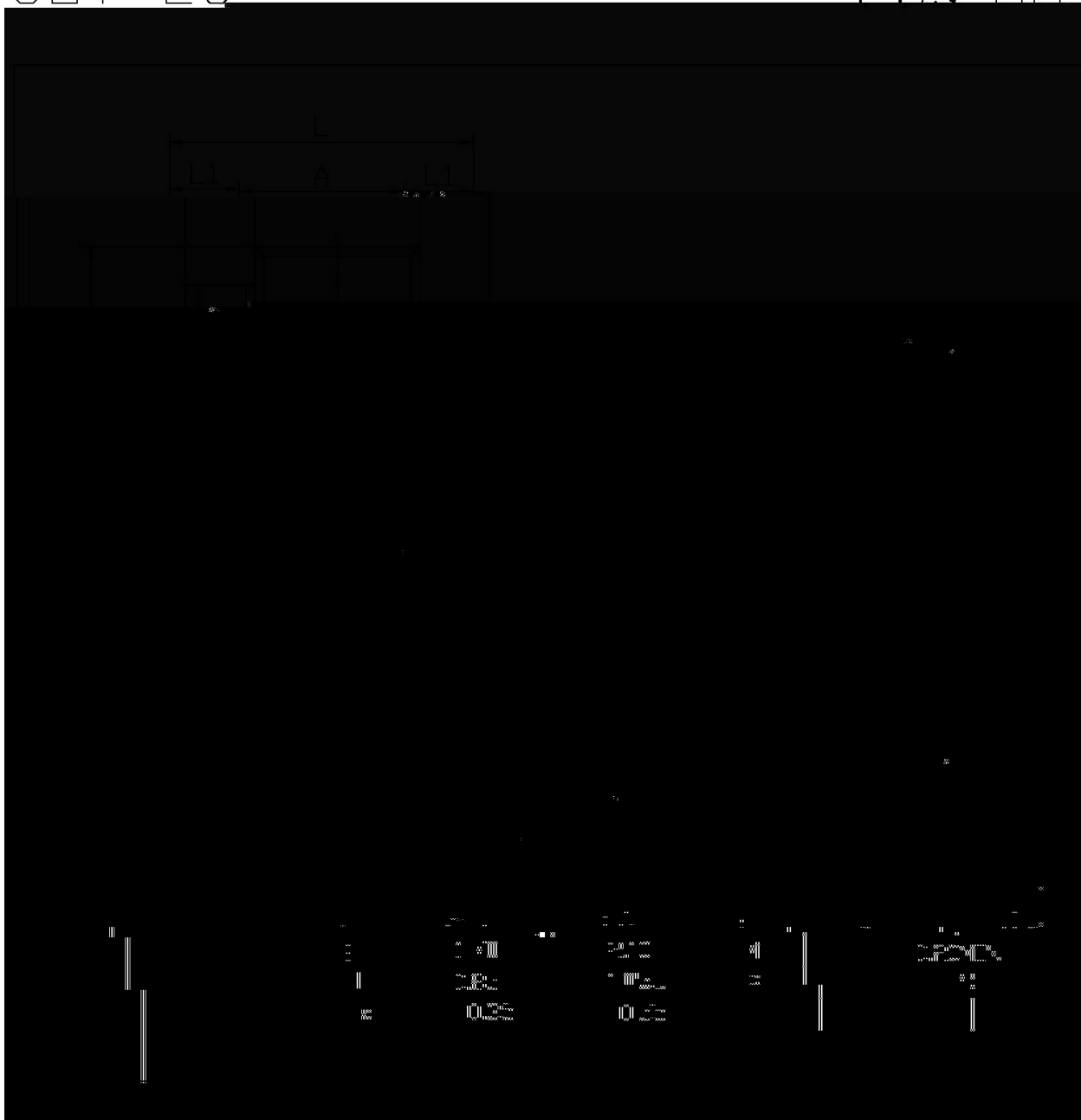
Electrical Characteristic Curve



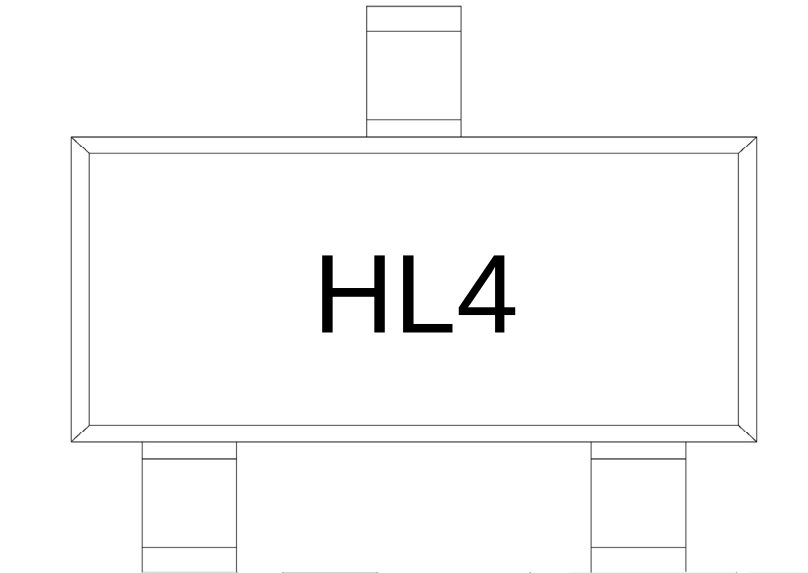
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



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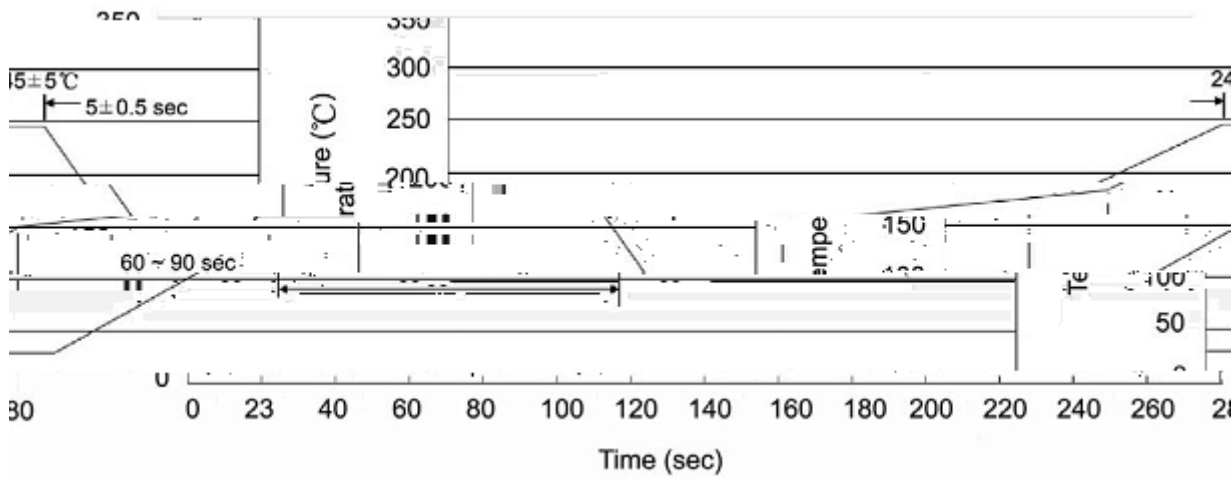
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Note:

H: Company Code.

L4: Product Type Code

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Note:

- 1

25 150%

60 90sec;

1.Preheating:25~150%, Time:60~90sec.
- 2

245±5%

5±0.5sec;

2.Peak Temp.:245±5%, Duration:5±0.5sec.
- 3

2 10%/sec.

3. Cooling Speed: 2~10%/sec.

/ Resistance to Soldering Heat Test Conditions

260±5%

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices